NSN 5962-01-373-6591

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1.2 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius **Storage Tempurature Range:** -65.0/+150.0 degrees celsius

Maximum Power Dissipation Rating:

Features Provided:

Ultraviolet erasable and programmed and monolithic

Inclosure Material:

Ceramic

Inclosure Configuration:

Flat pack

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Case Outline Source And Designator:

F-16 mil-m-38510

Current Rating Per Characteristic:

16.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, memory, digital cmos uv erasable pal

Voltage Rating And Type Per Characteristic:

-0.5 volts applied and 7.0 volts applied

Time Rating Per Chacteristic:

25.00 nanoseconds access

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). And 96906-mil-std-1835 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

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Specification Data:

67268-5962-8753901ka government standard and 94987-258480-8 manufacturers source control

Departure From Cited Designator:

Altered by programming & marking

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Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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